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NTE375 Silicon NPN Transistor TV Vertical Output (Compl to NTE398)

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	200V
Collector–Emitter Voltage, V_{CEO}	150V
Emitter–Base Voltage, V_{EBO}	6V
Collector Current, I_C	
Continuous	2A
Peak	10A
Collector Dissipation ($T_A = +25^\circ\text{C}$), P_C	1.75W
Collector Dissipation ($T_C = +25^\circ\text{C}$), P_C	25W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	–40° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 180V, I_E = 0$	–	–	1.0	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	–	–	5.0	mA
DC Current Gain	h_{FE}	$V_{CE} = 2V, I_C = 500mA$	100	–	200	
Gain Bandwidth Product	f_T	$V_{CE} = 5V, I_C = 500mA$	–	8	–	MHz
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1A, I_B = 100mA$	–	–	1.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 1A, I_B = 100mA$	–	–	1.8	V

